

Product Version 5.8 March 2018

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# **Contents**

About This Manual5
How This Document Is Organized5
Related Documents
Totalog Doginiono
1
<u></u>
New Features
<u> Overview</u>
Multi-Mask Patterning Technology
New LEF Features
LEF Layers Support Masks9
Fixed Masks for Layers and Macros
LEF Via Adds Masks for Fixed Vias 9
Macro Layer Geometries Support Masks
New DEF Features
Routing Blockages Add Mask Information
Component Mask Shift Multi-Patterning Layers
Components Adds Mask Shift Information
Fills Adds Masks
Nets Routing Points Enhancements
Special Nets Special Wiring Enhancements
DEF Via Adds Mask
Tracks Adds Mask
Pins Adds Mask
Blockages Change Component, Pushdown, Exceptpgnet to be Independent And Not
Exclusive

## **About This Manual**

This document provides information on new and changed features for version 5.8 of the Cadence<sup>®</sup> Library Exchange Format (LEF) and Design Exchange Format (DEF) integrated circuit description languages.

## **How This Document Is Organized**

This What's New document is organized into the following chapters:

New Features

This chapter describes features that were added or changed since version 5.7 of LEF and DEF.

New features are those that introduce new functionality into LEF and DEF. Any enhancements made to existing statements to support a new feature are also described in this chapter.

## **Related Documents**

The following documents provide detailed information about LEF and DEF, and the LEF and DEF application programming interfaces.

- <u>DEF C/C++ Programming Interface (Open Licensing Program)</u>
- <u>LEF C/C++ Programming Interface (Open Licensing Program)</u>
- <u>LEF/DEF Language Reference</u>
- What's New in DEF C/C++ Programming Interface
- What's New in LEF C/C++ Programming Interface

2/6/18

About This Manual

## **New Features**

- Overview on page 8
  - Multi-Mask Patterning Technology on page 8
- New LEF Features on page 9
  - □ <u>LEF Layers Support Masks</u> on page 9
  - □ Fixed Masks for Layers and Macros on page 9
  - □ <u>LEF Via Adds Masks for Fixed Vias</u> on page 9
  - □ Macro Layer Geometries Support Masks on page 10
- New DEF Features on page 12
  - □ Routing Blockages Add Mask Information on page 12
  - Component Mask Shift Multi-Patterning Layers on page 12
  - Components Adds Mask Shift Information on page 12
  - □ Fills Adds Masks on page 13
  - □ Nets Routing Points Enhancements on page 13
  - Special Nets Special Wiring Enhancements on page 14
  - □ DEF Via Adds Mask on page 15
  - □ Tracks Adds Mask on page 16
  - □ Pins Adds Mask on page 16
  - □ Blockages Change Component, Pushdown, Exceptpgnet to be Independent And Not Exclusive on page 17

**New Features** 

## **Overview**

## **Multi-Mask Patterning Technology**

The multi-mask patterning technology allows you to define multi-mask patterns for layers. You can define multi-mask statements that split a single layer into two or three masks. The syntax enhancements made to LEF/DEF v5.8 support more than three masks, though most applications support two or three masks only.

The subsequent sections describe the new syntax changes that have been made to incorporate this new feature.

**New Features** 

## **New LEF Features**

The following sections describe the enhancements that have been made to support multimask patterning for LEF.

## **LEF Layers Support Masks**

The MASK statement was added to specify how many masks for double- or triple-patterning will be used for a specified layer. You can use this statement for layers - cut, routing, implant, overlap, and/or masterslice.

Includes the following new syntax (in bold):

```
LAYER layerName

TYPE ROUTING; #or TYPE CUT, IMPLANT, MASTERSLICE, OVERLAP

[MASK numMasks;]
```

#### **Fixed Masks for Layers and Macros**

Some technologies do not allow mask shifting for cells using multi-mask patterning, e.g., pin and routing shapes are all pre-colored and must not be shifted to other masks. The FIXEDMASK statement was added to indicate that mask shifting is not allowed. All the LEF macro pin mask assignments are kept fixed and cannot be shifted to a different mask.

Includes the following new syntax (in bold):

```
For layers:
```

```
FIXEDMASK ;
  LAYER <statement>

For macros:
  MACRO macroName
     [CLASS className [subclassName] ;]
     [FIXEDMASK ;]
```

#### LEF Via Adds Masks for Fixed Vias

For fixed vias - rectangle or polygon - the masks in the via-master for cut layer are required for multi-cut vias. The VIARULE statement was enhanced to include masks. The MASK

**New Features** 

statement indicates which mask for double- or triple-patterning lithography is to be applied to the shapes defined using the RECT or POLYGON statements of the via master.

Includes the following new syntax (in bold):

```
VIA viaName [DEFAULT]
    { VIARULE viaRuleName ;
       CUTSIZE xSize vSize ;
       LAYERS botMetalLayer cutLayer topMetalLayer;
       CUTSPACING xCutSpacing yCutSpacing;
       ENCLOSURE xBotEnc yBotEnc xTopEnc yTopEnc;
       [ROWCOL numCutRows numCutCols;]
       [ORIGIN xOffset yOffset;]
        [OFFSET xBotOffset yBotOffset xTopOffset yTopOffset ;]
        [PATTERN cutPattern;]
    | [RESISTANCE resistValue ;]
     {LAYER layerName;
       { RECT [MASK maskNum] pt pt;
        | POLYGON [MASK maskNum] pt pt pt ...; } ...
     } . . .
    [PROPERTY propName propVal ;] ...
END viaName
```

## Macro Layer Geometries Support Masks

Macro layer geometries support multi-mask patterning. Three different masks can be added to the same layer geometries. The MASK statement was added to indicate which mask from double- or triple-patterning is to be used for path, rectangle, polygon, or via geometries.

```
{ LAYER layerName
        [EXCEPTPGNET]
        [SPACING minSpacing | DESIGNRULEWIDTH value];
    [WIDTH width ;]
        { PATH [MASK maskNum] pt ...;
        | PATH [MASK maskNum] ITERATE pt ... stepPattern;
        | RECT [MASK maskNum] pt pt;
        | RECT [MASK maskNum] ITERATE pt pt stepPattern;
        | POLYGON [MASK maskNum] pt pt pt pt ...;
        | POLYGON [MASK maskNum] ITERATE pt pt pt pt pt ... stepPattern;
```

New Features

```
} ...
| VIA [MASK viaMaskNum] pt viaName;
| VIA ITERATE [MASK viaMaskNum] pt viaName stepPattern;
} ...
```

For syntax information, see <u>"LEF Syntax"</u> chapter in the *LEF/DEF Language Reference*.

## **New DEF Features**

The following sections describe the enhancements that have been made to support multimask patterning for DEF.

#### **Routing Blockages Add Mask Information**

The BLOCKAGES section was enhanced to include masks. The MASK statement indicates which mask for double- or triple-patterning lithography is to be used for the specified shapes.

Includes the following new syntax (in bold):

## **Component Mask Shift Multi-Patterning Layers**

The COMPONENTMASKSHIFT statement defines which layers of a component are allowed to be shifted from the original mask colors in the LEF. This can be useful to shift all the layers of a specific component in order to align the masks with other component or router mask settings to increase routing density. This definition allows a specific component to compactly describe the mask shifting for that component.

Includes the following new syntax:

```
[COMPONENTMASKSHIFT layer1 [layer2 ...];]
```

## **Components Adds Mask Shift Information**

Some applications require the ability to "shift" the mask of pins and obstructions on a certain layer for a specific component to better align the pin masks with the routing masks.

The MASKSHIFT statement was added to allow shifting of the cell-master masks used in double- or triple-patterning for specific layers of an instance of the cell-master.

New Features

#### Includes the following new syntax (in bold):

#### Fills Adds Masks

In order to support multi-patterning technologies up to three different masks for the same layer can be added.

The MASK statement was added to specify which mask for double- or triple-patterning lithography is to be applied to the specified rectangles, polygons, or via shapes on each layer.

Includes the following new syntax (in bold):

## **Nets Routing Points Enhancements**

#### **Nets Adds Rectangle and/or Virtual Connection**

The NETS section was enhanced to provide the ability to create a rectangle or add a virtual connection to maintain the symbolic routing graph.

**New Features** 

The RECT statement allows creating a rectangle from the previous routing points. The VIRTUAL statement indicates that there is a virtual connection between the previous point and the new routing point.

Includes the following new syntax (in bold):

#### **Nets Adds Masks**

The NETS section routing points was enhanced to add masks - up to three different masks for the same layer can be added.

Includes the following new syntax (in bold):

```
{ ( x y [extValue] )
    [MASK maskNum] ( x y [extValue] )
    | [MASK viaMaskNum] viaName [orient]]
    | [MASK maskNum] RECT ( deltax1 deltay1 deltax2 deltay2 )
    | VIRTUAL ( x y ) } } ...
```

## **Special Nets Special Wiring Enhancements**

To support multi-mask patterning up to three different masks for the same layers can be added to special nets.

A new VIA statement was added to make it more efficient to specify several power-vias.

Additionally, the route status - cover, fixed, routed, shield, and shape - can be applied to polygons, rectangles, and vias.

```
[ [+ COVER | + FIXED | + ROUTED | + SHIELD shieldNetName]
        [+ SHAPE shapeType] [+ MASK maskNum]
        + POLYGON layerName pt pt pt ...
        | + RECT layerName pt pt
        | + VIA viaName [orient] pt ...
] {+ COVER | + FIXED | + ROUTED | + SHIELD shieldNetName}
        layerName routeWidth
```

**New Features** 

[DO numX BY numY STEP stepX stepY]

#### **DEF Via Adds Mask**

} . . .

For fixed vias, rectangle or polygon, the masks in the via-master for cut-layer shapes are required for multi-cut vias. The MASK statement indicates which mask for double- or triple-patterning lithography is to be applied to the defined shapes.

**New Features** 

#### **Tracks Adds Mask**

The routing tracks can now have mask assignments to aid alignment of routing masks inside a block with the level above. The MASK statement indicates which mask for double- or triple-patterning lithography to use for the first routing track.

Includes the following new syntax (in bold):

#### **Pins Adds Mask**

The PINS syntax has been modified in include mask attributes. The MASK statement indicates which mask from double- or triple-patterning to use for pins or via shapes on each layer.

```
[PINS numPins ;
[ [- pinName + NET netName]
    [[+ PORT]
        [+ LAYER layerName
              [MASK maskNum]
              [SPACING minSpacing | DESIGNRULEWIDTH effectiveWidth]
                   pt pt
         | + POLYGON layerName
              [MASK maskNum]
              SPACING minSpacing | DESIGNRULEWIDTH effectiveWidth]
                   pt pt pt ...
         |+ VIA viaName
              [MASK viaMaskNum]
                   рt
         1 ...
         [+ COVER pt orient | FIXED pt orient | PLACED pt orient]
    1...
; ] ...
END PINS]
```

**New Features** 

# Blockages Change Component, Pushdown, Exceptpgnet to be Independent And Not Exclusive

The BLOCKAGES section was enhanced to allow a blockage to simultaneously have COMPONENT, PUSHDOWN, and EXCEPTPGNET statements with the other attributes. These statements are now independent and not exclusive. The meaning of the keywords is unchanged.

Includes the following syntax changes (in bold):

```
[BLOCKAGES numBlockages;
[- LAYER layerName
    [+ SLOTS | + FILLS]
    [ + PUSHDOWN]
    [ + EXCEPTPGNET]
    [+ COMPONENT compName]
    [+ SPACING minSpacing | + DESIGNRULEWIDTH effectiveWidth]
    [+ MASK maskNum]
        {RECT pt pt | POLYGON pt pt pt ...} ...
;] ...
[- PLACEMENT
    [ + SOFT | + PARTIAL maxDensity]
    [ + PUSHDOWN]
    [+ COMPONENT compName]
        {RECT pt pt} ...
    ;] ...
END BLOCKAGES
```

For syntax information, see "DEF Syntax" chapter in the LEF/DEF Language Reference.